

Features

- Split Gate Trench MOSFET Technology
- High Density Cell Design for Low R_{DS(on)}
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

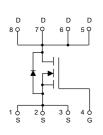
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient (Note 2)
- Thermal Resistance: 1.08°C/W Junction to Case

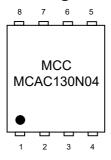
Parameter	Symbol	Rating	Unit		
Drain-Source Voltage	V _{DS}	40	V		
Gate-Source Volltage		V_{GS}	±20	V	
Continuous Drain Current	T _C =25°C		130	Α	
	T _C =100°C	_ I _D	82		
Pulsed Drain Current (Note 3)	I _{DM}	520	Α		
Total Power Dissipation (Note 4)		P _D	115	W	
Single Pulse Avalanche Energy (Note 5)		E _{AS}	600	mJ	

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C. The value in any given application depends on the user's specifi3023c board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. PD is based on max. junction temperature, using Steady-State junction-ambient thermal resistance.
- 5. TJ=25, V_{DD}=30V, V_{GS}=10V, L=3mH.

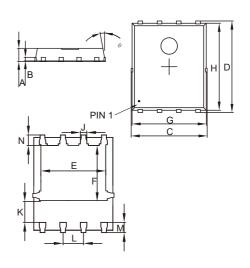
Internal Structure and Marking Code





N-CHANNEL MOSFET

DFN5060



	DIMENSIONS					
DIM	INC	INCHES		M	NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOIL	
Α	0.031	0.047	0.80	1.20		
В	0.010		0.254		TYP.	
С	0.193	0.222	4.90	5.64		
D	0.232	0.250	5.90	6.35		
E	0.148	0.167	3.75	4.25		
F	0.126	0.154	3.20	3.92		
G	0.189	0.213	4.80	5.40		
Н	0.222	0.239	5.65	6.06		
K	0.045	0.059	1.15	1.50		
J	0.012	0.020	0.30	0.50		
L	0.046	0.054	1.17	1.37		
М	0.012	0.028	0.30	0.71		
N	0.016	0.028	0.40	0.71		



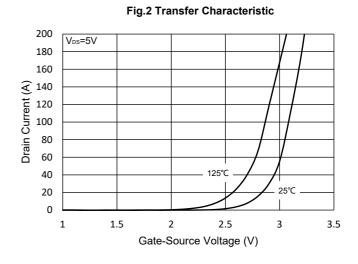
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

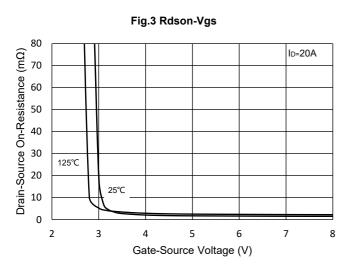
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			-	1			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	40			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1	μA	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.8	2.5	V	
		V _{GS} =10V, I _D =20A		1.45	1.75	1.75 2.5 mΩ	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =20A		1.9	2.5		
Gate Resistance	R _G	f=1MHz, Open Drain		2.6		Ω	
Dynamic Characteristics	-			1	ı		
Maximum Body-Diode Continuous Current	Is				130	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.2	V	
Reverse Recovery Charge	Q _{rr}	1 004 11/11 4004/		75		nC	
Reverse Recovery Time	t _{rr}	-I _F =20A,di/dt=100A/µs		57		ns	
Switching Characteristics					,		
Input Capacitance	C _{iss}			6853		pF	
Output Capacitance	C _{oss}	V _{DS} =20V,V _{GS} =0V,f=1MHz		1489			
Reverse Transfer Capacitance	C _{rss}			107			
Total Gate Charge	Q _g			125		nC	
Gate-Source Charge	Q _{gs}	V _{GS} =10V,V _{DS} =20V,I _D =20A		18			
Gate-Drain Charge	Q_{gd}			26			
Turn-On Delay Time	t _{d(on)}			12		ns	
Turn-On Rise Time	t _r	V _{GS} =10V,V _{DS} =20V,		34			
Turn-Off Delay Time	t _{d(off)}	I_{DS} =20A, R_{GEN} =2.2 Ω		139			
Turn-Off Fall Time	t _f			68			

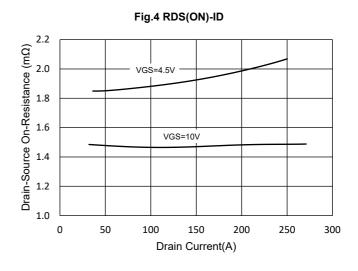


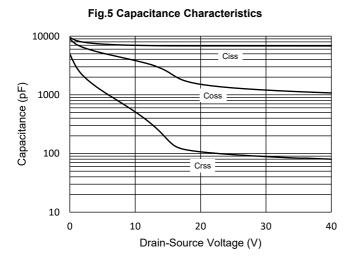
Curve Characteristics

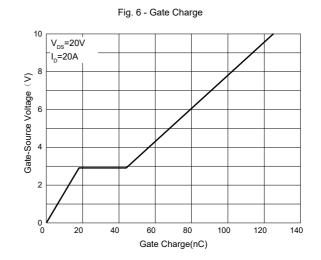
Fig. 1 - Typical Output Characteristics 250 V_{GS}=10V 8V 6V 200 4.5V 4V Drain Current (A) 3.5V 150 2.5V 100 50 0 0 1 4 5 Drain to Source Voltage(V)





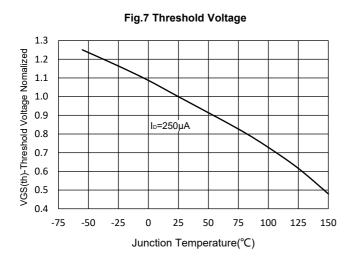


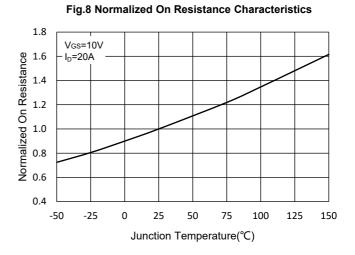


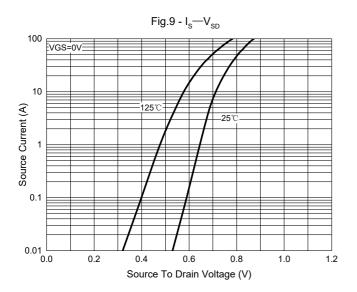


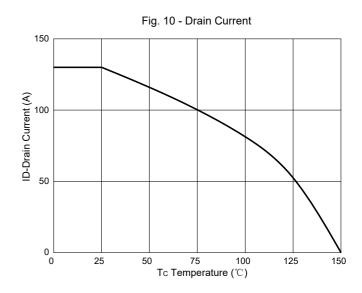


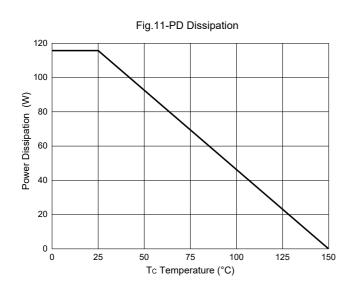
Curve Characteristics













Curve Characteristics

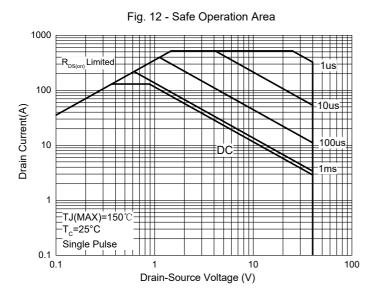
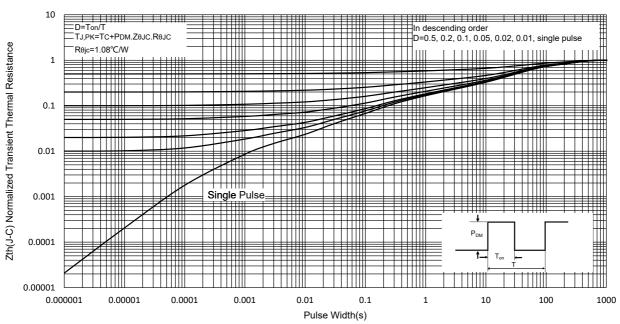


Fig.13 Normalized Transient Thermal Impedance





Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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